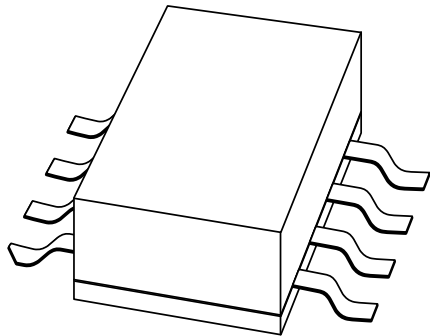


# DATA SHEET



## **BLF404** UHF power MOS transistor

Product specification  
Supersedes data of 1997 Oct 28

1998 Jan 29

# UHF power MOS transistor

# BLF404

### FEATURES

- High power gain
- Easy power control
- Gold metallization
- Good thermal stability
- Withstands full load mismatch
- Designed for broadband operation.

### APPLICATIONS

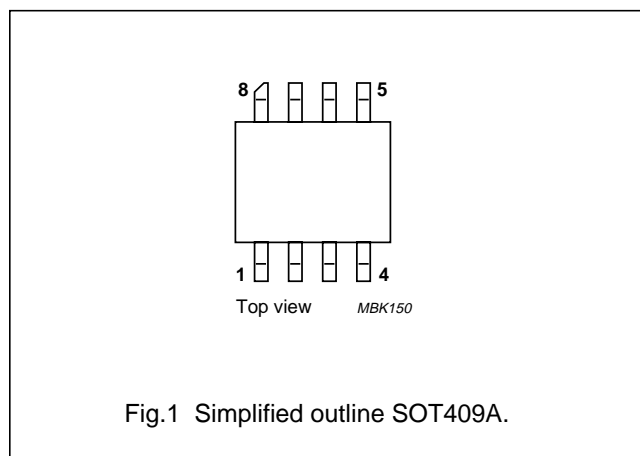
- Communication transmitters in the VHF/UHF range with a nominal supply voltage of 12.5 V.

### DESCRIPTION

Silicon N-channel enhancement mode vertical D-MOS power transistor in an 8-lead SOT409A SMD package with a ceramic cap.

### PINNING

PIN	DESCRIPTION
1, 8	source
2, 3	gate
4, 5	source
6, 7	drain



### QUICK REFERENCE DATA

RF performance at  $T_{mb} \leq 60 \text{ }^\circ\text{C}$  in a common source test circuit.

MODE OF OPERATION	f (MHz)	V <sub>DS</sub> (V)	P <sub>L</sub> (W)	G <sub>p</sub> (dB)	$\eta_D$ (%)
CW class-AB	500	12.5	4	$\geq 10$	$\geq 50$

### CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A, and SNW-FQ-302B.

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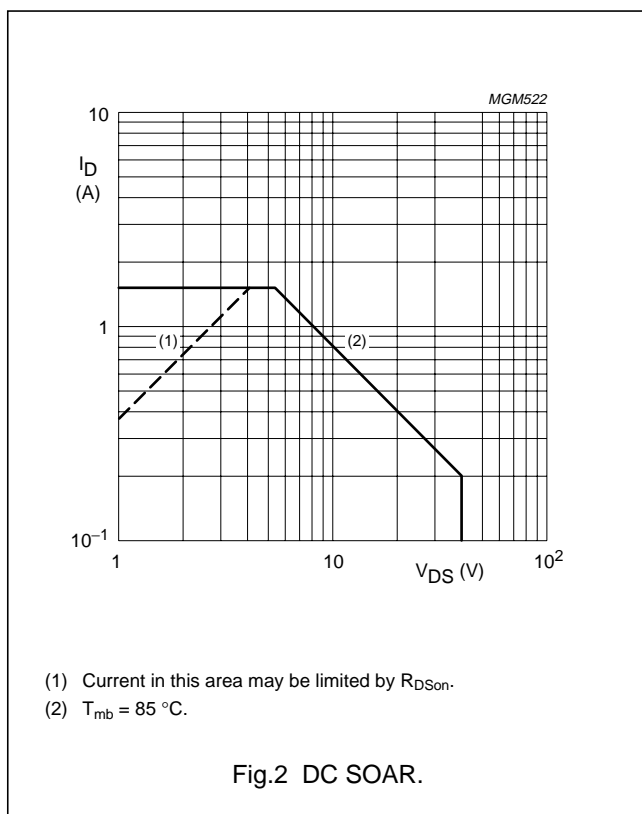
## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DS}$	drain-source voltage		–	40	V
$V_{GS}$	gate-source voltage		–	$\pm 20$	V
$I_D$	DC drain current		–	1.5	A
$P_{tot}$	total power dissipation	$T_{mb} \leq 85\text{ }^\circ\text{C}$	–	8.3	W
$T_{stg}$	storage temperature		–65	150	$^\circ\text{C}$
$T_j$	junction temperature		–	200	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_{mb} \leq 85\text{ }^\circ\text{C}, P_{tot} = 8.3\text{ W}$	12.1	K/W



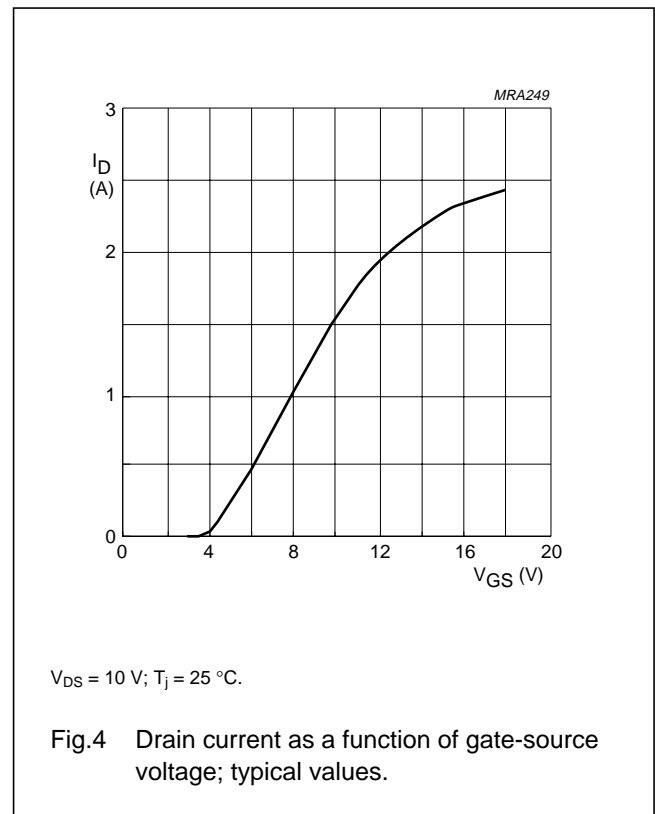
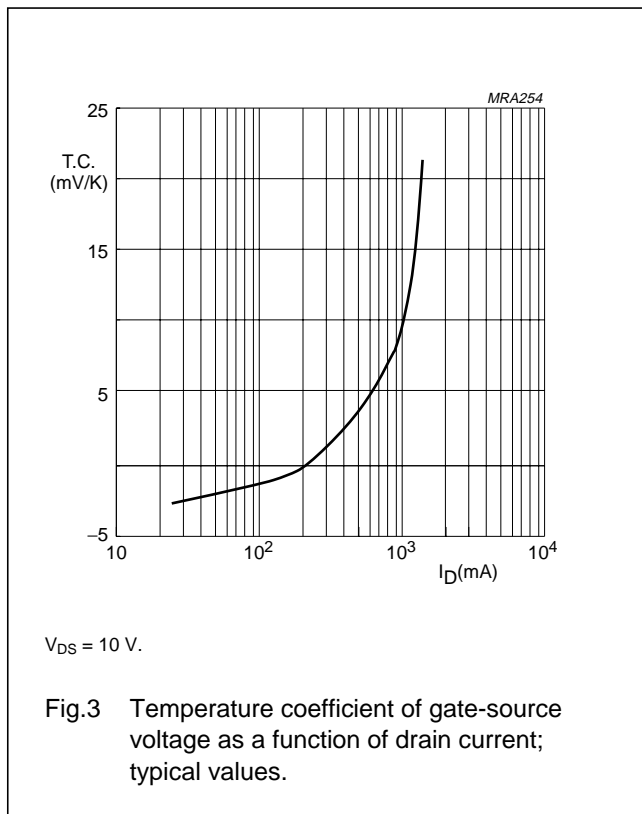
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**CHARACTERISTICS**

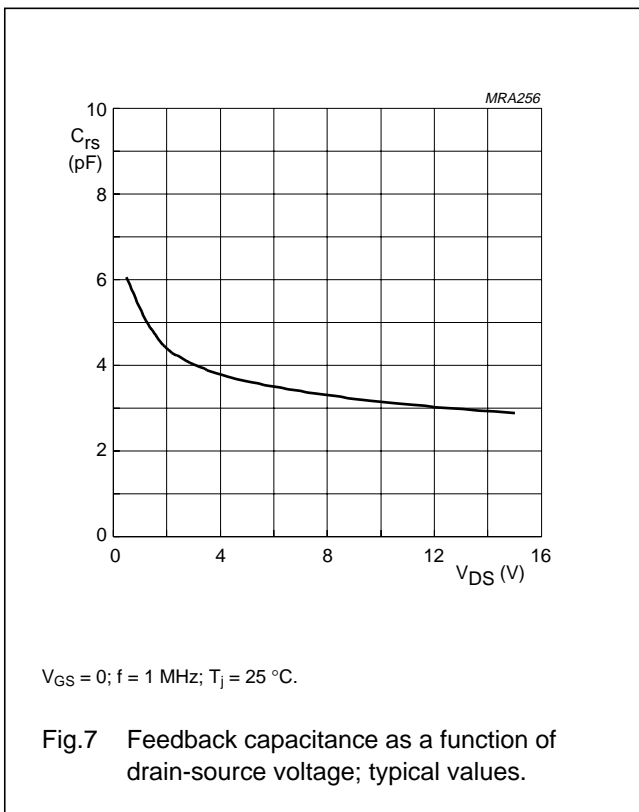
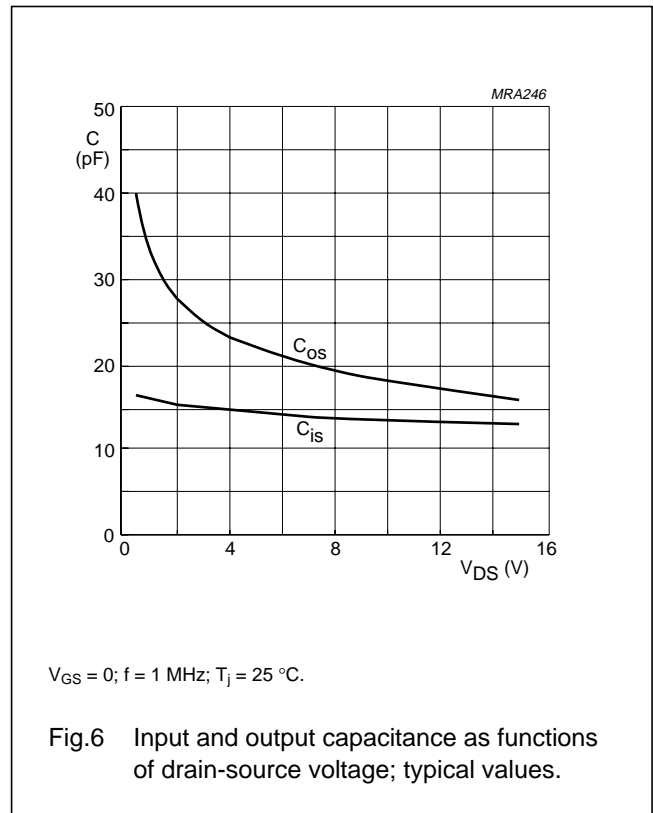
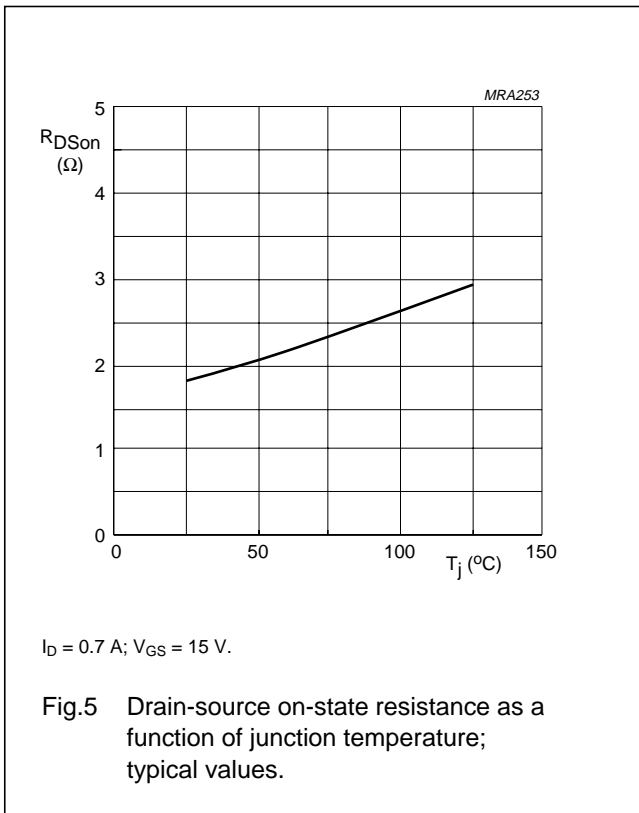
$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0; I_D = 5\text{ mA}$	40	–	–	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 50\text{ mA}; V_{DS} = 10\text{ V}$	2	–	4.5	V
$I_{DSS}$	drain-source leakage current	$V_{GS} = 0; V_{DS} = 12.5\text{ V}$	–	–	0.5	mA
$I_{GSS}$	gate-source leakage current	$V_{DS} = 0; V_{GS} = \pm 20\text{ V}$	–	–	1	$\mu\text{A}$
$I_{DSX}$	on-state drain current	$V_{GS} = 15\text{ V}; V_{DS} = 10\text{ V}$	–	2.3	–	A
$R_{DSon}$	drain-source on-state resistance	$I_D = 0.7\text{ A}; V_{GS} = 15\text{ V}$	–	1.8	2.7	$\Omega$
$g_{fs}$	forward transconductance	$I_D = 0.7\text{ A}; V_{DS} = 10\text{ V}$	200	270	–	mS
$C_{is}$	input capacitance	$V_{GS} = 0; V_{DS} = 12.5\text{ V}; f = 1\text{ MHz}$	–	14	–	pF
$C_{os}$	output capacitance	$V_{GS} = 0; V_{DS} = 12.5\text{ V}; f = 1\text{ MHz}$	–	17	–	pF
$C_{rs}$	feedback capacitance	$V_{GS} = 0; V_{DS} = 12.5\text{ V}; f = 1\text{ MHz}$	–	3	–	pF



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# UHF power MOS transistor

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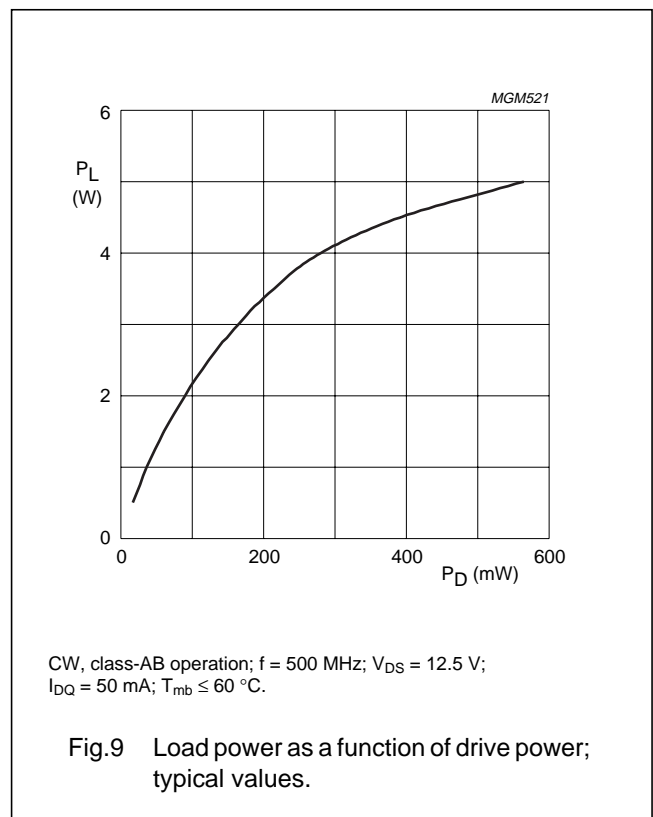
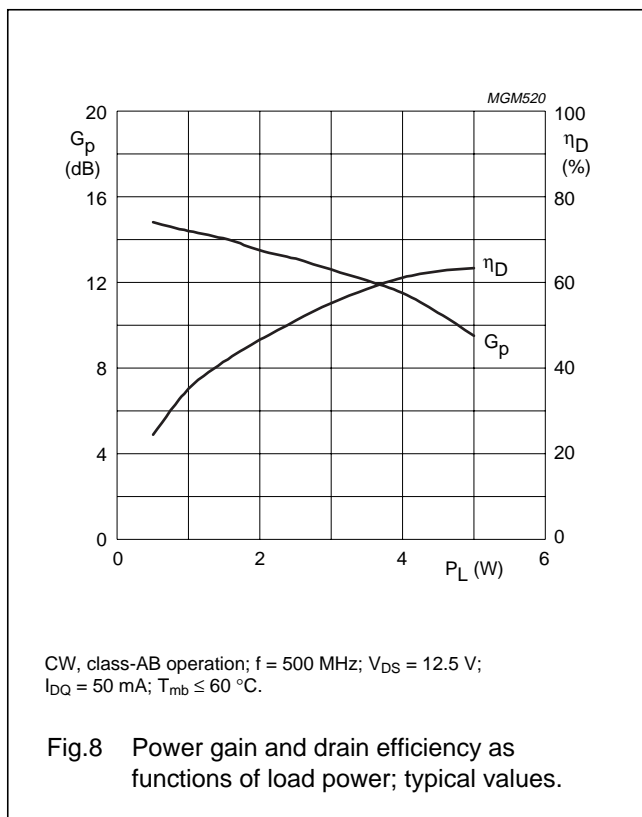
### APPLICATION INFORMATION

RF performance at  $T_{mb} \leq 60\text{ }^\circ\text{C}$  in a common source test circuit with the device soldered on a printed-circuit board with through metallized holes.

MODE OF OPERATION	f (MHz)	V <sub>DS</sub> (V)	I <sub>DQ</sub> (A)	P <sub>L</sub> (W)	G <sub>p</sub> (dB)	$\eta_D$ (%)
CW, class-AB	500	12.5	50	4	$\geq 10$ typ. 11.5	$\geq 50$ typ. 55

### Ruggedness in class-AB operation

The BLF404 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: f = 500 MHz; V<sub>DS</sub> = 12.5 V; P<sub>L</sub> = 4 W; T<sub>mb</sub> ≤ 60 °C.



# UHF power MOS transistor

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## Test circuit information

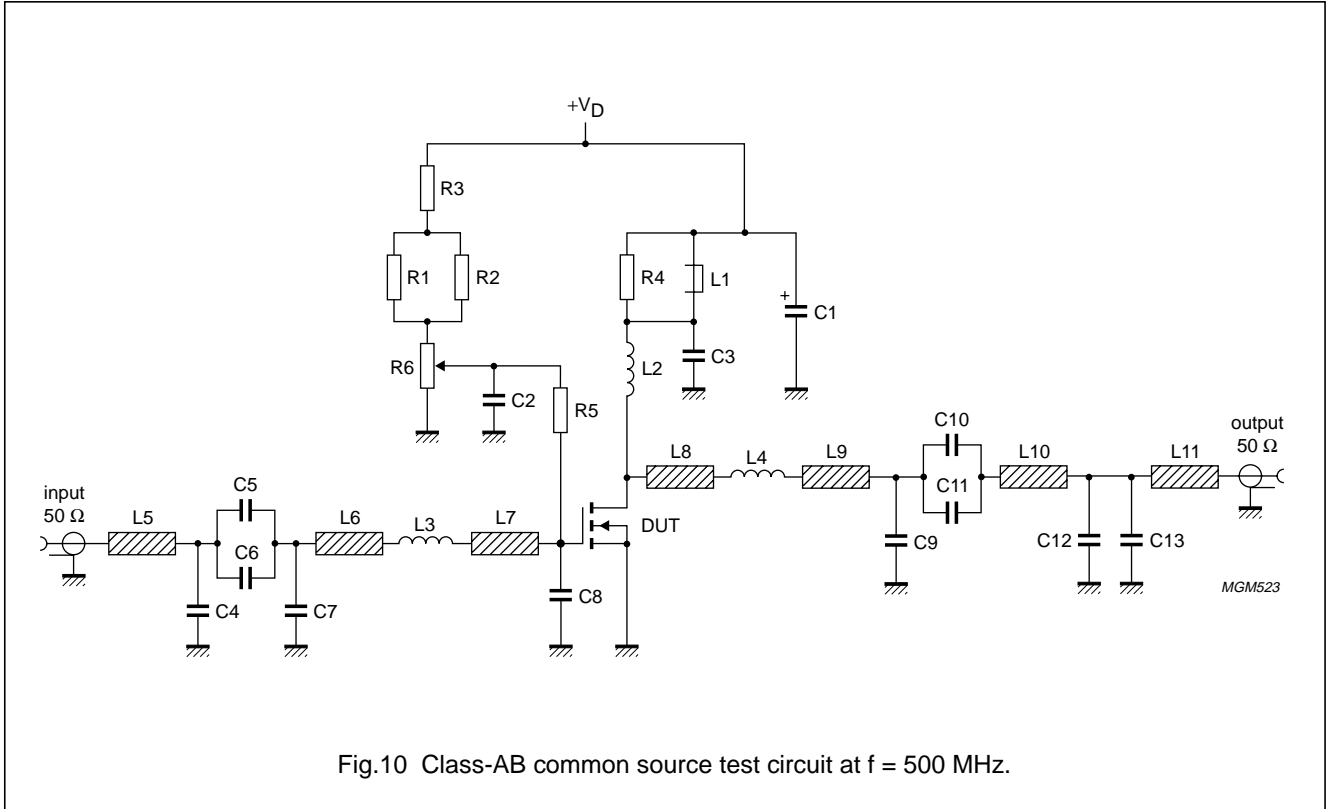


Fig.10 Class-AB common source test circuit at  $f = 500$  MHz.

## UHF power MOS transistor

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List of components used in test circuit (see Figs 10 and 11).

COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE No.
C1	electrolytic capacitor	4.7 $\mu$ F, 10 V		
C2, C3	multilayer ceramic chip capacitor	47 nF		
C4	multilayer ceramic chip capacitor; note 1	18 pF		
C5, C10	multilayer ceramic chip capacitor; note 1	180 pF		
C6, C11	multilayer ceramic chip capacitor; note 1	270 pF		
C7	multilayer ceramic chip capacitor; note 1	22 pF		
C8	multilayer ceramic chip capacitor; note 1	8.2 pF		
C9	multilayer ceramic chip capacitor; note 1	2.7 pF		
C12	multilayer ceramic chip capacitor; note 1	1.2 pF		
C13	multilayer ceramic chip capacitor; note 1	12 pF		
L1	2 turns 1 mm enamelled copper wire on a grade 4B1 Ferroxcube core		ext. dia. = 4.2 mm int. dia. = 2 mm length = 6 mm	
L2	3 turns 1 mm enamelled copper wire		int. dia. = 4.6 mm leads = 2 x 5 mm	
L3	bifilar coil		lead dia. = 0.8 mm	
L4	bifilar coil		lead dia. = 1 mm	
L5	stripline; note 2	50 $\Omega$	8.8 x 2.38 mm	
L6	stripline; note 2	50 $\Omega$	5.8 x 2.38 mm	
L7	stripline; note 2	50 $\Omega$	6.8 x 2.38 mm	
L8	stripline; note 2	50 $\Omega$	3.76 x 2.38 mm	
L9	stripline; note 2	50 $\Omega$	5.8 x 2.38 mm	
L10	stripline; note 2	50 $\Omega$	4.48 x 2.38 mm	
L11	stripline; note 2	50 $\Omega$	3.13 x 2.38 mm	
R1, R2	SMD resistor	3.9 k $\Omega$		
R3	metal film resistor	1 k $\Omega$ , 0.25 W		
R4	metal film resistor	22 $\Omega$ , 0.25 W		
R5	metal film resistor	10 k $\Omega$ , 0.25 W		
R6	potentiometer	10 k $\Omega$		

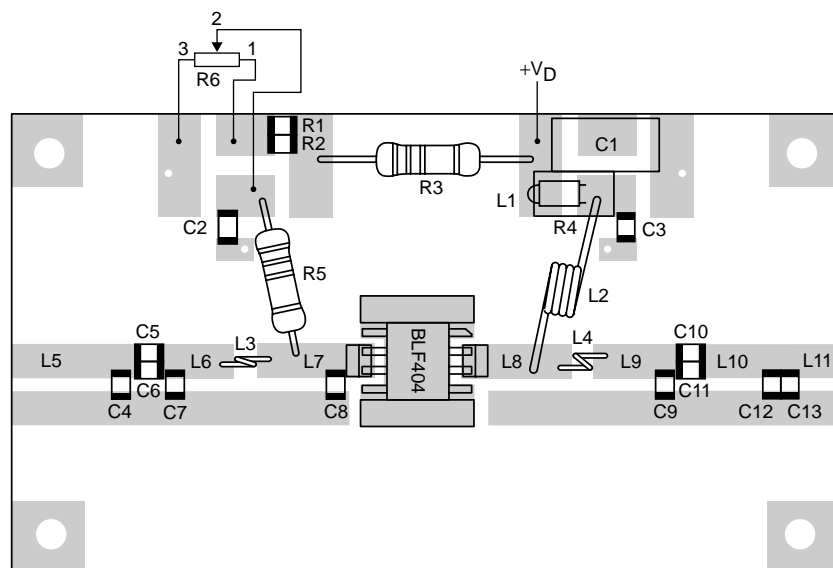
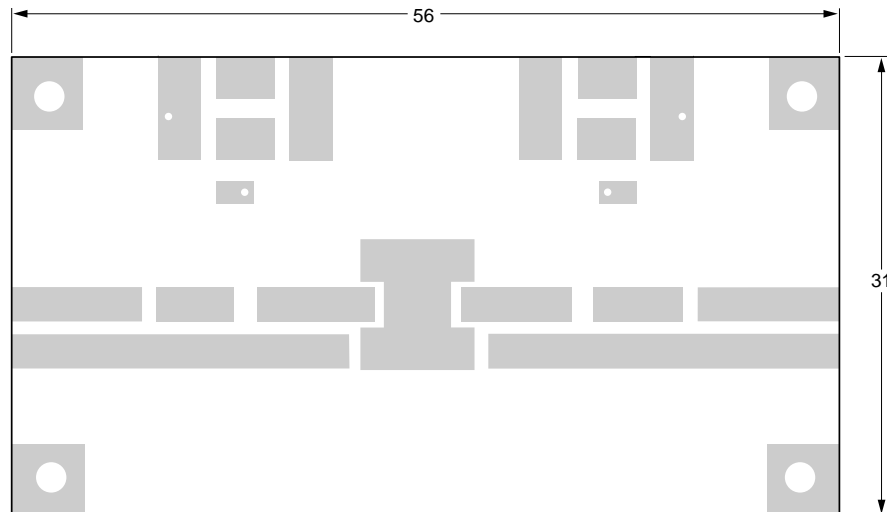
**Notes**

- American Technical Ceramics type 100A or capacitor of same quality.
- The striplines are on a double copper-clad printed circuit board, with DUROID dielectric ( $\epsilon_r = 2.2$ ); thickness 0.79 mm, thickness of the copper sheet 2 x 35  $\mu$ m.



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MGM524

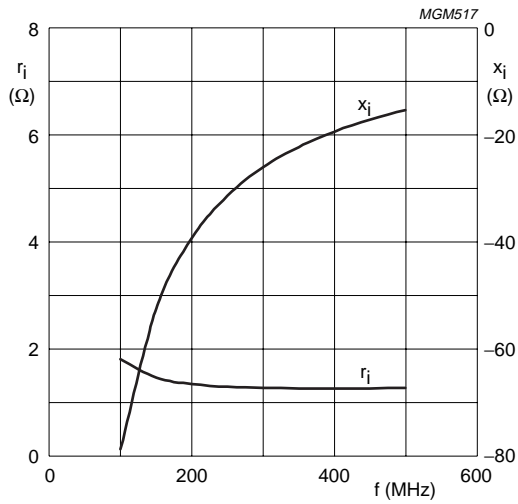
Dimensions in mm.

The components are situated on one side of the copper-clad printed-circuit board, the other side is unetched and serves as a ground plane. Earth connections from the component side to the ground plane are made by through metallization.

Fig.11 Printed-circuit board and component layout for 500 MHz class-AB test circuit in Fig.10.

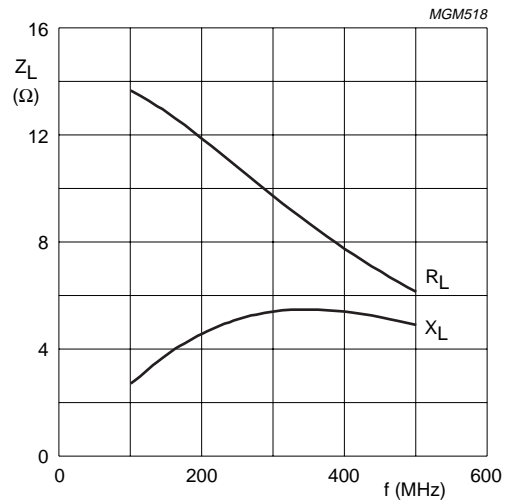
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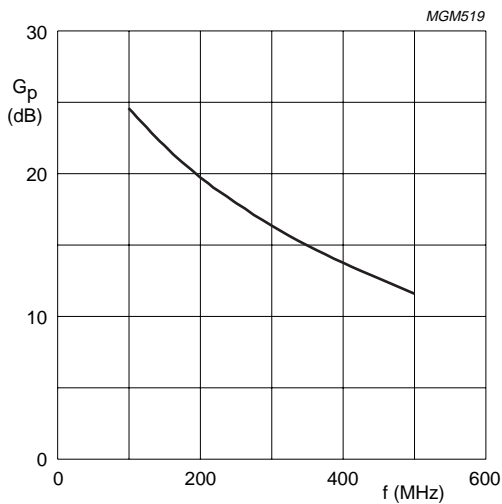
CW, class-AB operation;  $V_{DS} = 12.5$  V;  $I_D = 50$  mA;  
 $P_L = 4$  W;  $T_{mb} \leq 60$  °C.

Fig.12 Input impedance as a function of frequency (series components); typical values.



CW, class-AB operation;  $V_{DS} = 12.5$  V;  $I_D = 50$  mA;  
 $P_L = 4$  W;  $T_{mb} \leq 60$  °C.

Fig.13 Load impedance as a function of frequency (series components); typical values.



CW, class-AB operation;  $V_{DS} = 12.5$  V;  $I_{DQ} = 50$  mA;  
 $P_L = 4$  W;  $T_{mb} \leq 60$  °C.

Fig.14 Power gain as a function of frequency (series components); typical values.

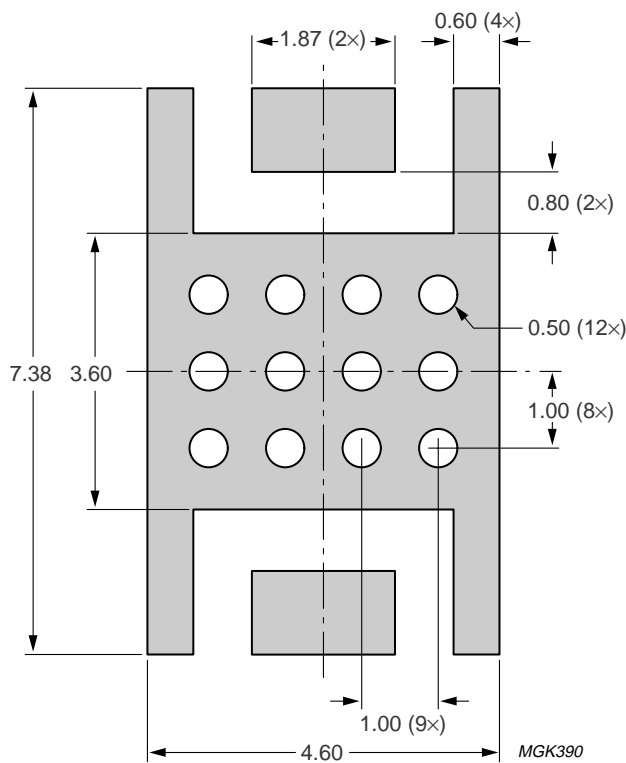
UHF power MOS transistor

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**MOUNTING RECOMMENDATIONS**

Both the metallized groundplate and leads contribute to the heatflow. It is recommended that the transistor is mounted on a grounded metallized area of a maximum thickness of 0.8 mm on the printed-circuit board, equipped with at least 12 (0.5 mm diameter) through metallized holes filled with solder.

A thermal resistance  $R_{th(mb-h)}$  of 5 K/W can be achieved if heatsink compound is applied when the transistor is mounted on the printed-circuit board.



Dimensions in mm.

Fig.15 Reflow soldering footprint for SOT409A.

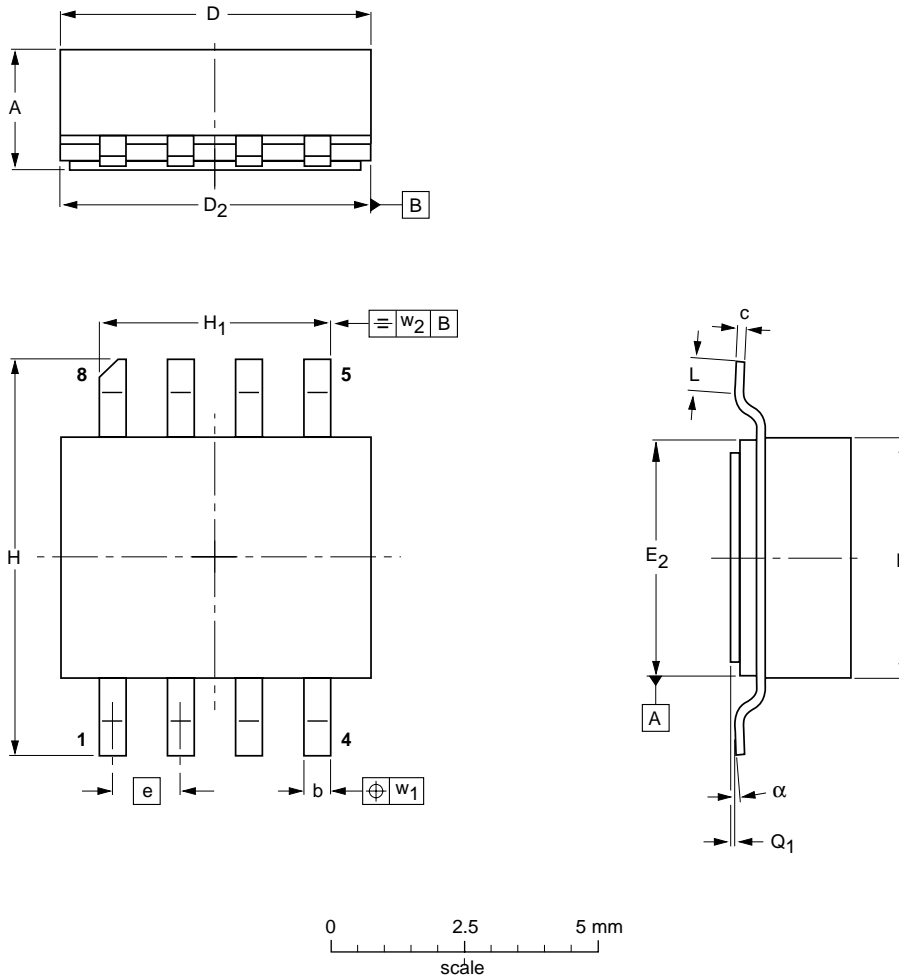
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PACKAGE OUTLINE

Ceramic surface mounted package; 8 leads

SOT409A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D <sub>2</sub>	E	E <sub>2</sub>	e	H	H <sub>1</sub>	L	Q <sub>1</sub>	w <sub>1</sub>	w <sub>2</sub>	$\alpha$
mm	2.36 2.06	0.58 0.43	0.23 0.18	5.94 5.03	5.16 5.00	4.93 4.01	4.14 3.99	1.27	7.47 7.26	4.39 4.24	1.02 0.51	0.10 0.00	0.25	0.25	7° 0°
inches	0.093 0.081	0.023 0.017	0.009 0.007	0.234 0.198	0.203 0.197	0.194 0.158	0.163 0.157	0.050	0.294 0.286	0.173 0.167	0.040 0.020	0.004 0.000	0.010	0.010	7° 0°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT409A						98-01-27

## UHF power MOS transistor

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**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

**LIFE SUPPORT APPLICATIONS**

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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**NOTES**

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**NOTES**

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